

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:19
L2	1	"257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:19
L3	2	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:19
L4	89	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:21
L5	1	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:21
S1	0	(SiN same ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD"))) and (("SiO.sub.2") same (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:10

S2	0	(SiN with ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")))) and (("SiO.sub.2") with (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:10
S3	0	(SiN and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")))) and (("SiO.sub.2") and (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:11
S4	0	((Silicon adj nitride) or ("SiN")) and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")) and (("SiO.sub.2") and (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:13
S5	70	((Silicon adj nitride) or ("SiN")) and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:21
S6	79	((("SiO.sub.2") and (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:21
S7	16	((("SiO.sub.2") same (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:21
S8	8	((("SiO.sub.2") with (dip adj etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/01 08:21
S11	79	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:20
S12	38	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 08:14

S15	54	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:08
S16	10	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 08:20
S17	36	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and (dop\$6 or implant\$6) and (oxygen or ("O.sub.2"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 08:22
S18	12	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 08:35
S19	5	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((dop\$6 or implant\$6) with (oxygen or ("O.sub.2")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 08:35
S20	12	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (silicon adj carbide)) or ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:21

S21	10	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC")) or ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:25
S22	2	438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC")) or ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:33
S23	36	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:36
S24	35	"257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 09:27
S25	50	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:36
S26	8	438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 09:24

S27	36	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:41
S28	35	"257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/27 13:44
S29	50	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:15
S30	5	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:30
S31	10	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:26
S32	3032	semiconductor and ((dop\$6 or implant\$6) with ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:27
S33	4829	semiconductor and ((dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:28
S34	794	semiconductor and ((dop\$6 or implant\$6) near ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:29

S35	2013	semiconductor and ((doped) with ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:28
S36	4050	semiconductor and ((doped or implant\$6) same ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:29
S37	676	semiconductor and ((doped or implant\$6) near ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:29
S38	3172	semiconductor and ((doped) same ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:29
S39	544	semiconductor and ((doped) near ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:30
S40	3172	semiconductor and ((doped) same ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:30
S41	0	semiconductor with ((chemical adj mechanical adj polish\$6) or ("CMP")) with ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) with ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:31
S42	0	semiconductor near ((chemical adj mechanical adj polish\$6) or ("CMP")) near ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) near ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:32
S43	0	semiconductor near ((chemical adj mechanical adj polish\$6) or ("CMP")) near ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) near ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:32

S44	2	semiconductor same ((chemical adj mechanical adj polish\$6) or ("CMP")) same ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) same ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 07:32
S46	280	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 09:24
S47	8	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 09:28
S48	4	"257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 10:26
S49	300	438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 09:31
S50	22	"438"/\$.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 10:26
S51	18	"257"/\$.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/28 10:26
S59	1875	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 14:17

S68	612	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 14:17
S69	28	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/20 14:06
S70	7	438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/25 12:25
S71	28	"438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj1 carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/25 12:13
S72	38	semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj1 carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/25 12:20
S73	7	438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/25 12:25

S76	29	(("20040048468") or ("20020063334") or ("20020115285") or ("6261951") or ("6642145") or ("6432822") or ("6429128") or ("6140226") or ("6593660") or ("6649531") or ("6656840") or ("6737747") or ("6566242") or ("6362085") or ("6656644") or ("6620633") or ("6380555") or ("4532150") or ("4854263") or ("5238866") or ("5465680") or ("5773100") or ("5989623") or ("6040022") or ("6100559") or ("6174810") or ("6365518") or ("4029522") or ("5877513")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/28 10:44
S77	1	("20040097072").PN.	US-PGPUB; USPAT	OR	OFF	2005/01/28 10:44